TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOSVI-H)

# **TPCA8052-H**

Switching Regulator Applications Motor Drive Applications DC-DC Converter Applications

- · Small footprint due to a small and thin package
- High-speed switching
- Small gate charge: Q<sub>SW</sub> = 6.8 nC (typ.)
- Low drain-source ON-resistance:  $R_{DS (ON)} = 7.2 \text{ m}\Omega \text{ (typ.)}$
- High forward transfer admittance: |Yfs| = 58 S (typ.)
- Low leakage current:  $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 40 \text{ V)}$
- Enhancement mode:  $V_{th}$  = 1.3 to 2.3 V ( $V_{DS}$  = 10 V,  $I_D$  = 0.2 mA)

### Absolute Maximum Ratings (Ta = 25°C)

| Characte                 | eristic                         | Symbol           | Rating     | Unit |  |
|--------------------------|---------------------------------|------------------|------------|------|--|
| Drain-source voltage     |                                 | $V_{DSS}$        | 40         | V    |  |
| Drain-gate voltage (R    | GS = 20 kΩ)                     | $V_{DGR}$        | 40         | V    |  |
| Gate-source voltage      |                                 | V <sub>GSS</sub> | ±20        | V    |  |
| Drain current            | DC (Note 1)                     | ID               | 20         | Α    |  |
| Drain current            | Pulsed (Note 1) I <sub>DP</sub> | $I_{DP}$         | 60         | Α    |  |
| Drain power dissipati    | on (Tc = 25°C)                  | $P_{D}$          | 30         | W    |  |
| Drain power dissipati    | on (t = 10 s)<br>(Note 2a)      | $P_{D}$          | 2.8        | W    |  |
| Drain power dissipati    | on (t = 10 s)<br>(Note 2b)      | P <sub>D</sub>   | 1.6        | W    |  |
| Single-pulse avalance    | ne energy<br>(Note 3)           | E <sub>AS</sub>  | 37         | mJ   |  |
| Avalanche current        |                                 | I <sub>AR</sub>  | 20         | Α    |  |
| Repetitive avalanche (To | energy<br>c = 25°C) (Note 4)    | E <sub>AR</sub>  | 2.24       | mJ   |  |
| Channel temperature      |                                 | T <sub>ch</sub>  | 150        | °C   |  |
| Storage temperature      | range                           | T <sub>stg</sub> | -55 to 150 | °C   |  |

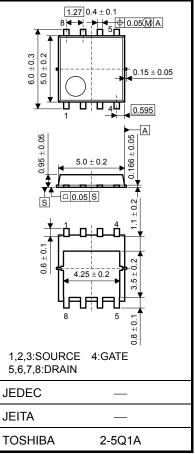
Note: For Notes 1 to 4, refer to the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e.

operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

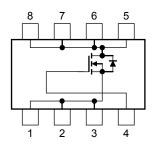
This transistor is an electrostatic-sensitive device. Handle with care.

Unit: mm



Weight: 0.069 g (typ.)

#### **Circuit Configuration**

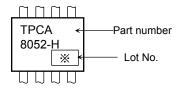


Start of commercial production 2009-03

#### **Thermal Characteristics**

| Characteristic  | Symbol                 | Max  | Unit |
|---|------------------------|------|------|
| Thermal resistance, channel to case (Tc = 25°C)                       | R <sub>th (ch-c)</sub> | 4.17 | °C/W |
| Thermal resistance, channel to ambient (t = 10 s) (Note 2a)           | R <sub>th (ch-a)</sub> | 44.6 | °C/W |
| Thermal resistance, channel to ambient $(t = 10 \text{ s})$ (Note 2b) | R <sub>th (ch-a)</sub> | 78.1 | °C/W |

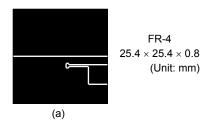
### Marking (Note 5)

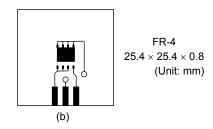


Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)





Note 3: V<sub>DD</sub> = 24 V, T<sub>ch</sub> = 25 °C (initial), L = 100  $\mu$ H, R<sub>G</sub> = 25  $\Omega$ , I<sub>AR</sub> = 20 A

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: \* Weekly code: (Three digits)



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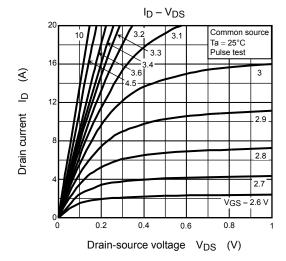
# **Electrical Characteristics (Ta = 25°C)**

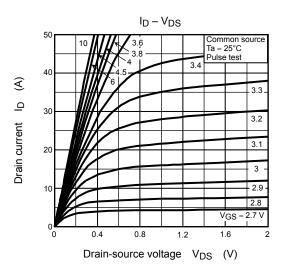
| Characteristic                 |                  | Symbol                | Test Condition   | Min                     | Тур. | Max     | Unit |
|--------------------------------|------------------|-----------------------|--|-------------------------|------|---------|------|
| Gate leakage cur               | rent             | I <sub>GSS</sub>      | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$                        | _                       | _    | ±100    | nA   |
| Drain cutoff curre             | nt               | I <sub>DSS</sub>      | V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 0 V                            | _                       | _    | 10      | μА   |
| Drain source broa              | akdowa voltago   | V <sub>(BR) DSS</sub> | $I_D = 10$ mA, $V_{GS} = 0$ V  | -   -   10   40   -   - | _    | V       |      |
| Drain-source breakdown voltage |                  | V <sub>(BR) DSX</sub> | $I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$                            | 23                      | _    | _       | V    |
| Gate threshold vo              | oltage           | V <sub>th</sub>       | $V_{DS} = 10 \text{ V}, I_D = 0.2 \text{ mA}$                            | 1.3                     | _    | 2.3     | V    |
| Drain-source ON-resistance     |                  | Б                     | $V_{GS} = 4.5 \text{ V}, I_D = 10 \text{ A}$                             |                         | 9.1  | 13.1    | - mΩ |
|                                |                  | R <sub>DS</sub> (ON)  | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A                            | _                       | 7.2  | 11.3    |      |
| Forward transfer               | admittance       | Y <sub>fs</sub>       | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 10 A                            | 29                      | 58   | _       | S    |
| Input capacitance              |                  | C <sub>iss</sub>      |  |                         | 1620 | 2110    | pF   |
| Reverse transfer capacitance   |                  | C <sub>rss</sub>      | V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz                 | _                       | 85   | 130     |      |
| Output capacitance             |                  | Coss                  |  | _                       | 280  | _       |      |
| Gate resistance                |                  | rg                    | $V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 5 \text{ MHz}$         |                         | 2.3  | 2.3 3.5 |      |
| Switching time                 | Rise time        | t <sub>r</sub>        | VGS 0 V  |                         | 2.4  |         | - ns |
|                                | Turn-on time     | t <sub>on</sub>       |  | _                       | 8.4  | _       |      |
|                                | Fall time        | t <sub>f</sub>        |  | _                       | 8.0  | _       |      |
|                                | Turn-off time    | t <sub>off</sub>      | $V_{DD} \approx 20 \text{ V}$ Duty $\leq$ 1%, $t_W = 10 \mu\text{s}$     | _                       | 35   | _       |      |
| Total gate charge              | otal gate charge |                       | $V_{DD} \approx 32 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$ |                         | 25   |         |      |
| (gate-source plus              | gate-drain)      | Qg                    | $V_{DD} \approx 32 \text{ V}, V_{GS} = 5 \text{ V}, I_D = 20 \text{ A}$  | _                       | _ 13 |         |      |
| Gate-source charge 1           |                  | Q <sub>gs1</sub>      |  | _                       | 5.6  | _       | nC   |
| Gate-drain ("Miller") charge   |                  | Q <sub>gd</sub>       | $V_{DD} \approx 32 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$ |                         | 3.8  | _       |      |
| Gate switch charge             |                  | Q <sub>SW</sub>       |  | _                       | 6.8  | _       |      |

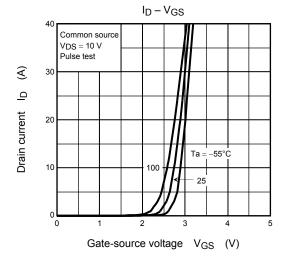
## **Source-Drain Ratings and Characteristics (Ta = 25°C)**

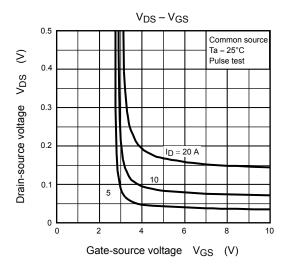
| Characteristic          |       | Symbol   | Test Condition   | Min   | Тур. | Max | Unit |   |
|-------------------------|-------|----------|------------------|---|------|-----|------|---|
| Drain reverse current   | Pulse | (Note 1) | I <sub>DRP</sub> | _   | _    | _   | 60   | Α |
| Forward voltage (diode) |       |          | $V_{DSF}$        | $I_{DR} = 20 \text{ A}, V_{GS} = 0 \text{ V}$ |      | _   | -1.2 | V |

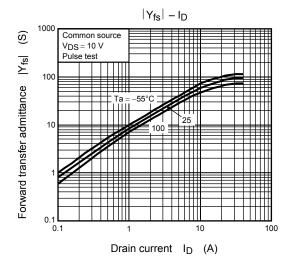
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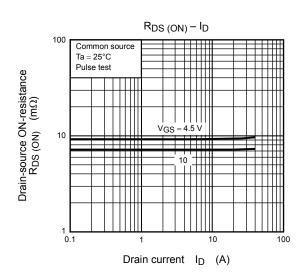


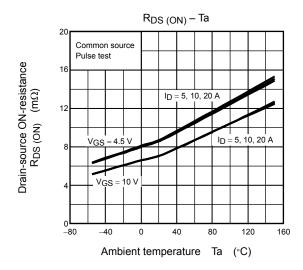


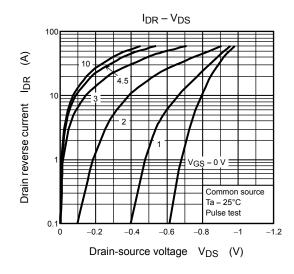


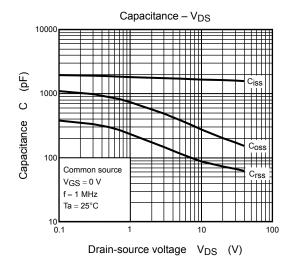


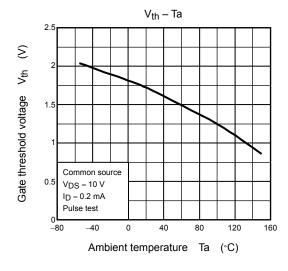


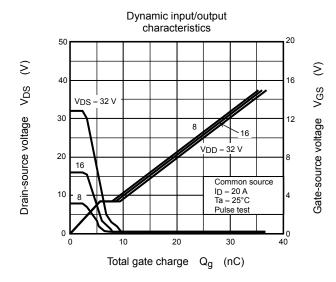


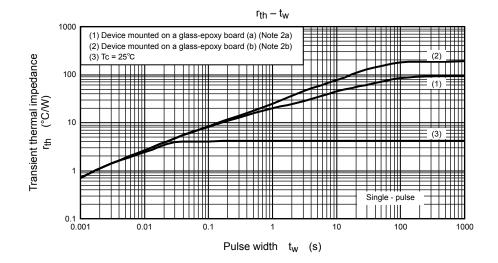


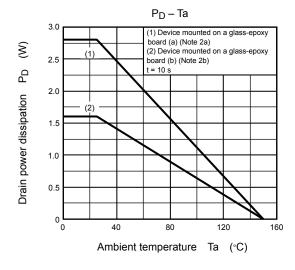


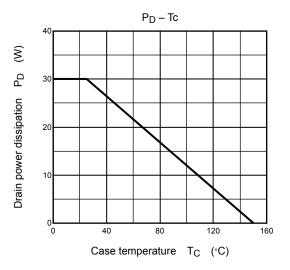


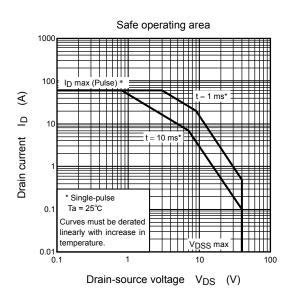












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